



1.1 Scope.

This specification covers the detail requirements for a monolithic CMOS 8-bit input/output port. This consists of an 8-bit sampling analog-to-digital converter, an 8-bit digital-to-analog converter with output amplifier, and a common reference and 8-bit parallel data bus.

1.2 Part Number.

The complete part numbers per Tables 1 and 2 of this specification are as follows:

Device	Part Number
-1	AD7569S(X)/883B
-2	AD7569T(X)/883B

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline:

(X)	Package	Description
Q	Q-24	24-Pin Cerdip
E	E-28A	28-Contact LCC

1.3 Absolute Maximum Ratings. ($T_A = +25^\circ\text{C}$)

V_{DD} to AGND (DAC or ADC)	-0.3 V, +7 V
V_{DD} to DGND	-0.3 V, +7 V
V_{DD} to V_{SS}	-0.3 V, +14 V
AGND (DAC or ADC) to DGND	-0.3 V, $V_{DD} + 0.3$ V
AGND (DAC) to AGND (ADC)	± 5 V
Logic Voltage to DGND	-0.3 V, $V_{DD} + 0.3$ V
CLK Input Voltage to DGND	-0.3 V, $V_{DD} + 0.3$ V
V_{OUT} to AGND (DAC)	$V_{SS} - 0.3$ V, $V_{DD} + 0.3$ V
V_{IN} to AGND (ADC)	$V_{SS} - 0.3$ V, $V_{DD} + 0.3$ V
Power Dissipation (to $+75^\circ\text{C}$)	450 mW
Derates above $+75^\circ\text{C}$	6 mW/ $^\circ\text{C}$
Operating Temperature Range	-55°C to $+125^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (Soldering 10 sec)	$+300^\circ\text{C}$

1.5 Thermal Characteristics.

Thermal Resistance $\theta_{JC} = 35^\circ\text{C}/\text{W}$ for Q-24 and E-28A
 $\theta_{JA} = 120^\circ\text{C}/\text{W}$ for Q-24 and E-28A

AD7569—SPECIFICATIONS

Table 1.

DAC	Symbol	Device	Design Limit $T_{min}-T_{max}$	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition ¹ /Comments	Units
Resolution	RES	-1, 2	8				Minimum Resolution for Which No Missing Codes Are Guaranteed.	Bits
Total Unadjusted Error	TUE	-1, 2	3					±LSB typ
Relative Accuracy	INL	-1	1	1	1			±LSB max
		-2	1/2	1	1/2	1/2		
Differential Nonlinearity	DNL	-1	1	1	1			±LSB max
		-2	3/4	1	3/4	3/4		
Unipolar Offset Error		-1	2.5	2	2.5			±LSB max
		-2	2	2	2	1.5		
Bipolar Zero Offset Error		-1	2.5	2	2.5			±LSB max
		-2	2	2	2	1.5		
Full-Scale Error ²		-1	4	2	4			LSB max
		-2	3	2	3	1		
Δ Full Scale/ ΔV_{DD}		-1, 2		1/2			$V_{OUT} = 2.5 \text{ V}; \Delta V_{DD} = \pm 5\%$	±LSB max
Δ Full Scale/ ΔV_{SS}		-1, 2		1/2			$V_{OUT} = -2.5 \text{ V}; \Delta V_{SS} = \pm 5\%$	±LSB max
Signal-to-Noise Ratio	SNR	-1	44	44	44		$V_{OUT} = 20 \text{ kHz Sine}; f_{SAMPLING} = 400 \text{ kHz}$	dB min
		-2	46	46	46			
Total Harmonic Distortion	THD	-1, 2	48	48	48		$V_{OUT} = 20 \text{ kHz Sine}; f_{SAMPLING} = 400 \text{ kHz}$	dB max
Intermodulation Distortion	IMD	-1, 2	55				$f_a = 18.4 \text{ kHz}; f_b = 14.5 \text{ kHz}; f_{SAMPLING} = 400 \text{ kHz}$	dB typ
Digital Input Low Voltage	V_{IL}	-1, 2	0.8	0.8	0.8			V max
Digital Input High Voltage	V_{IH}	-1, 2	2.4	2.4	2.4			V min
Unipolar Analog Output Voltage		-1, 2	0 to +1.25/2.5					
Bipolar Analog Output Voltage		-1, 2	±1.25/±2.5					
Input Leakage Current	I_{IN}	-1, 2	10	10	10		$V_{IN} = 0 \text{ to } V_{DD}$	±μA max
Input Capacitance	C_{IN}	-1, 2	10					pF max
Supply Current from V_{DD}	I_{DD}	-1, 2	13	13	13			mA max
Supply Current from V_{SS}	I_{SS}	-1, 2	4	4	4			mA max

NOTES

¹ $V_{DD} = +5 \text{ V} \pm 5\%$, $V_{SS} = \text{RANGE} = \text{AGND}_{DAC} = \text{AGND}_{ADC} = \text{DGND} = 0 \text{ V}$, $f_{CLK} = 5 \text{ MHz}$

²Includes internal voltage reference error and is calculated after offset error has been adjusted out.

查询"AD7569TQ/883B"供应商

Table 2.

ADC	Test	Symbol	Device	Design Limit $T_{min}-T_{max}$	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition ¹ /Comments	Units
	Resolution	RES	-1, 2	8				Minimum Resolution for Which No Missing Codes Are Guaranteed.	Bits
	Total Unadjusted Error	TUE	-1, 2	4					$\pm$ LSB typ
	Relative Accuracy	INL	-1	1	1	1			$\pm$ LSB max
			-2	1/2	1	1/2	1/2		
	Differential Nonlinearity	DNL	-1	1	1	1			$\pm$ LSB max
			-2	3/4	1	3/4	3/4		
	Unipolar Offset Error		-1	3	2	3			$\pm$ LSB max
			-2	2.5	2	2.5	1.5		
	Bipolar Zero Offset Error		-1	4	3	4			$\pm$ LSB max
			-2	3.5	3	3.5	2.5		
	Full-Scale Error ²		-1, 2	-7.5	-7.5	-7.5			LSB max
				+2	+2	+2			
	Δ Full Scale/ ΔV_{DD}		-1, 2		0.5			$V_{IN} = +2.5$ V; $\Delta V_{DD} = \pm 5\%$	$\pm$ LSB max
	Δ Full Scale/ ΔV_{SS}		-1, 2		0.5			$V_{IN} = -2.5$ V; $\Delta V_{SS} = \pm 5\%$	$\pm$ LSB max
	Signal-to-Noise Ratio	SNR	-1	44	44	44	44	$V_{IN} = 100$ kHz Sine; $f_{SAMPLING} = 400$ kHz	dB min
			-2	45	44	45	44		
	Total Harmonic Distortion	THD	-1, 2	48	48	48		$V_{IN} = 100$ kHz Sine; $f_{SAMPLING} = 400$ kHz	dB max
	Intermodulation Distortion	IMD	-1, 2	60				$f_a = 99$ kHz; $f_b = 96.7$ kHz; $f_{SAMPLING} = 400$ kHz	dB typ
	Digital Input Low Voltage	V_{IL}	-1, 2	0.8	0.8	0.8			V max
	Digital Input High Voltage	V_{IH}	-1, 2	2.4	2.4	2.4			V min
	Unipolar Analog Input Voltage	V_{INV}	-1, 2	0 to 1.25/+2.5				$V_{DD} = +5$ V; $V_{SS} = 0$ V	V
	Bipolar Analog Input Voltage	V_{INB}	-1, 2	$\pm 1.25/\pm 2.5$				$V_{DD} = +5$ V; $V_{SS} = -5$ V	V
	Input Current	I_{IN}	-1, 2	300	300	300			$\pm \mu$ A max
	Input Capacitance	C_{IN}	-1, 2	10					pF max
	Input Leakage Current	I_{IL}	-1, 2	10	10	10			$\pm \mu$ A max
	CLK Input Current (High Level)	I_{INH}	-1, 2	40	40	40		$V_{IN} = V_{DD}$	μ A max
	CLK Input Current (Low Level)	I_{INL}	-1, 2	-1.6	-1.6	-1.6		$V_{IN} = 0$ V	mA max
	Digital Output Low Voltage	V_{OL}	-1, 2	0.4	0.4	0.4			V max
	Digital Output High Voltage	V_{OH}	-1, 2	4.0	4.0	4.0			V min
	Floating State Leakage Current	I_{OUT}	-1, 2	10	10	10			$\pm \mu$ A max

AD7569

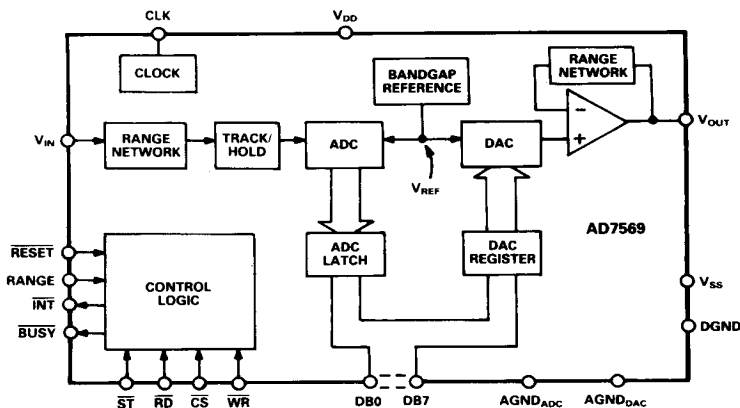
Test	Symbol	Device	Design Conditions $T_{min} - T_{max}$	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition ¹ /Comments	Units
Floating State Output Capacitance	C _{OUT}	-1, 2	10					pF max
Conversion Time (External Clock)	t _{CONV}	-1, 2	2.0	2.0	2.0		f _{CLK} = 5.0 MHz	μs max

NOTES

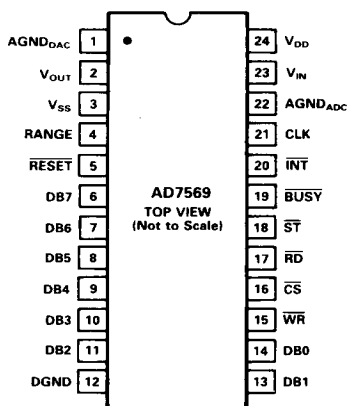
¹V_{DD} = +5 V ± 5%, V_{SS} = RANGE = AGND_{DAC} = AGND_{ADC} = DGND = 0 V, f_{CLK} = 5 MHz

²Includes internal voltage reference error and is calculated after offset error has been adjusted out.

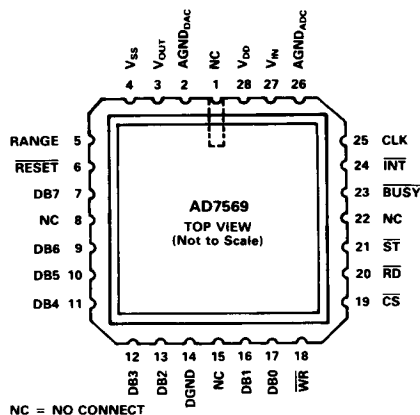
3.2.1 Functional Block Diagram and Terminal Assignments.



Q Package (DIP)



E Package (LCC)

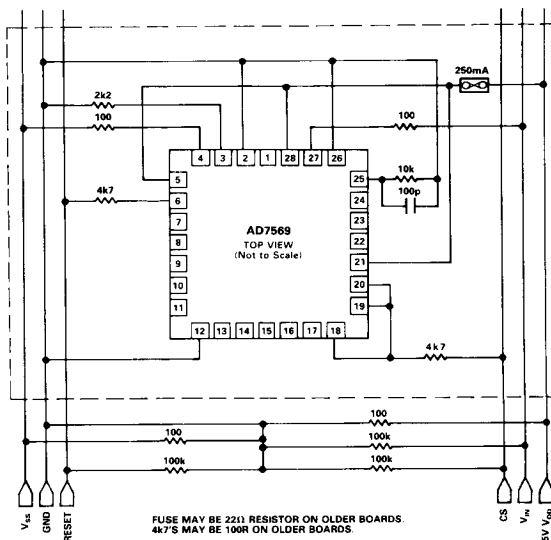
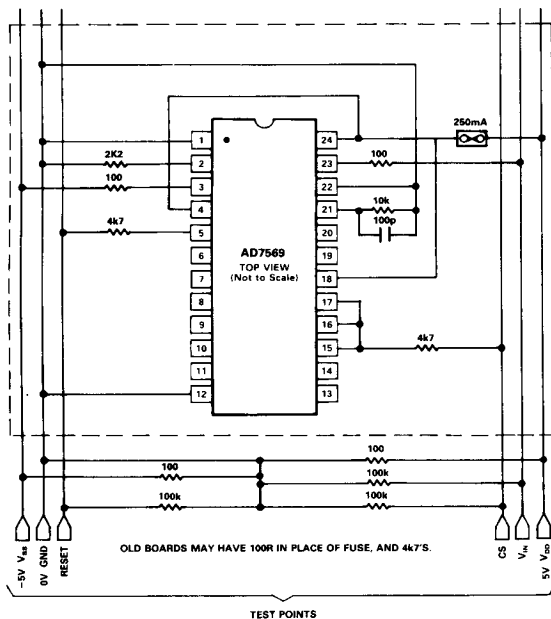


3.2.4 Microcircuit Technology Group.

查询"AD7569TQ/883B"供应商

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



AD7569 Edge Connections

TIMING¹

查询"AD7569TQ/883B"供应商

Test	Symbol	Device	Design Limit T _{min} to T _{max}	Units
DAC Timing				
$\overline{WR}$ Pulse Width	t_1	-1, 2	90	ns min
$\overline{CS}$, $\overline{A/B}$ to $\overline{WRS}$ Setup Time	t_2	-1, 2	0	ns min
$\overline{CS}$, $\overline{A/B}$ to $\overline{WR}$ Hold Time	t_3	-1, 2	0	ns min
Data Valid to $\overline{WR}$ Setup Time	t_4	-1, 2	80	ns min
Data Valid to $\overline{WR}$ Hold Time	t_5	-1, 2	10	ns min
ADC Timing				
$\overline{ST}$ Pulse Width	t_6	-1, 2	50	ns min
$\overline{ST}$ to $\overline{BUSY}$ Delay	t_7	-1, 2	150	ns max
$\overline{BUSY}$ to $\overline{INT}$ Delay	t_8	-1, 2	30	ns max
$\overline{BUSY}$ to $\overline{CS}$ Delay	t_9	-1, 2	0	ns min
$\overline{CS}$ to $\overline{RD}$ Setup Time	t_{10}	-1, 2	0	ns min
$\overline{RD}$ Pulse Width. Determined by t_{13} .	t_{11}	-1, 2	90	ns min
$\overline{CS}$ to $\overline{RD}$ Hold Time	t_{12}	-1, 2	0	ns min
Data Access Time after $\overline{RD}$; $C_L = 20$ pF	t_{13}^2	-1, 2	90	ns max
Data Access Time after $\overline{RD}$; $C_L = 100$ pF	t_{13}^2	-1, 2	135	ns max
Bus Relinquish Time after $\overline{RD}$	t_{14}^3	-1, 2	10	ns min
	t_{14}^3	-1, 2	85	ns max
$\overline{RD}$ to $\overline{INT}$ Delay	t_{15}	-1, 2	85	ns max
$\overline{RD}$ to $\overline{BUSY}$ Delay	t_{16}	-1, 2	160	ns max
Data Valid Time after $\overline{BUSY}$; $C_L = 20$ pF	t_{17}^2	-1, 2	90	ns max
Data Valid Time after $\overline{BUSY}$; $C_L = 100$ pF	t_{17}^2	-1, 2	135	ns max

NOTES
¹All input control signals are specified with $t_r = t_f = 5$ ns (10% to 90% of +5 V) and timed from a voltage level of 1.6 V.
² t_{13} and t_{17} are measured with the load circuits of Figure 1 and defined as the time required for an output to cross 0.8 V or 2.4 V.
³ t_{14} is defined as the time required for the data line to change 0.5 V when loaded with the circuit of Figure 2.

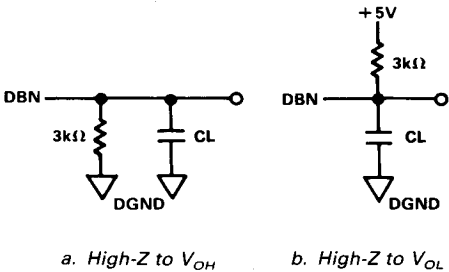


Figure 1. Load Circuits for Data Access Time Test

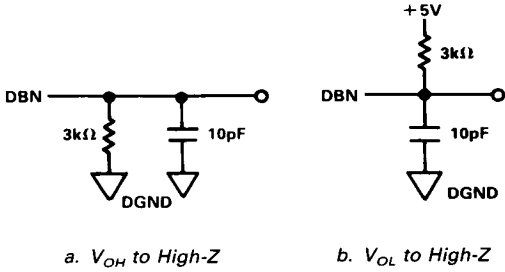


Figure 2. Load Circuits for Bus Relinquish Time Test